

HW-7

Xichen Li, EE521 - Group 5

A) Xichen Li: I did HW7 independently.

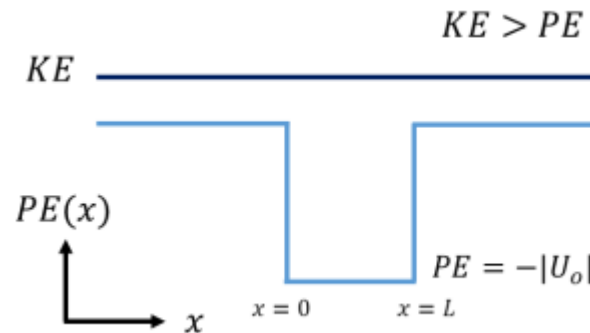
Chapter-10 P3 :

Assume an electron is moving to the right from $x < 0$, and it is facing a potential trough with a depth of $-|U_o|$. That is, $PE = -|U_o|$.

(a) Show that there will be a reflection at the trough and calculate the reflection (R) and transmission (T) coefficients.

(b) Plot the reflection and transmission probabilities in terms of $KE/|U_o|$, where KE is the kinetic energy of the incident electron.

Note that this problem is like the case of a potential barrier when $KE > PE$, discussed in this chapter. The only difference is that you can simply replace U_o with $-|U_o|$ in the corresponding equations for T and R .



Answer

(a) According to the definition of R and T :

$$R = \left| \frac{B}{A} \right|^2$$

$$T = \left| \frac{F}{A} \right|^2$$

Since $KE > PE$, the boundary condition needs to be re-written as:

$$\begin{aligned}
A + B &= C + D \\
ik(A - B) &= \alpha(C - D) \\
Ce^{\alpha L} + De^{-\alpha L} &= Fe^{i\beta L} \\
\alpha(Ce^{\alpha L} - De^{-\alpha L}) &= i\beta Fe^{i\beta L}
\end{aligned}$$

where

$$\begin{aligned}
k &= \sqrt{\frac{2mE}{\hbar^2}} \\
\alpha &= \sqrt{\frac{2m(-|U_o| - E)}{\hbar^2}} \\
\beta &= \sqrt{\frac{2mE}{\hbar^2}}
\end{aligned}$$

Note α is an imaginary number.

Then we can solve for B/A and F/A : And we also have :

$$\begin{aligned}
\frac{B}{A} &= \frac{(\alpha + i\beta)(\alpha - ik)e^{-\alpha L} - (\alpha - i\beta)(\alpha + ik)e^{\alpha L}}{(\alpha + i\beta)(\alpha + ik)e^{-\alpha L} - (\alpha - i\beta)(\alpha - ik)e^{\alpha L}} e^{-i\beta L} \\
\frac{F}{A} &= \frac{-4iak}{(\alpha + i\beta)(\alpha + ik)e^{-\alpha L} - (\alpha - i\beta)(\alpha - ik)e^{\alpha L}} e^{-i\beta L}
\end{aligned}$$

Because $\beta = k$, then B/A and F/A can be re-written as :

$$\begin{aligned}
\frac{B}{A} &= \frac{(\alpha^2 + k^2)(e^{-\alpha L} - e^{\alpha L})}{(\alpha + ik)^2 e^{-\alpha L} - (\alpha - ik)^2 e^{\alpha L}} e^{-ikL} \\
\frac{F}{A} &= \frac{-4iak}{(\alpha + ik)^2 e^{-\alpha L} - (\alpha - ik)^2 e^{\alpha L}} e^{-ikL}
\end{aligned}$$

Then T and R coefficients are:

$$\begin{aligned}
R &= \left| \frac{B}{A} \right|^2 = \left| \frac{(\alpha^2 + k^2)(e^{-\alpha L} - e^{\alpha L})}{(\alpha + ik)^2 e^{-\alpha L} - (\alpha - ik)^2 e^{\alpha L}} e^{-ikL} \right|^2 \\
T &= \left| \frac{F}{A} \right|^2 = \left| \frac{-4iak}{(\alpha + ik)^2 e^{-\alpha L} - (\alpha - ik)^2 e^{\alpha L}} e^{-ikL} \right|^2
\end{aligned}$$

As you can see from the expressions for R and T , there will still be reflection at the trough.

(b) Plot the reflection and transmission probabilities in terms of $E/|U_o|$

The R and T are plotted in Plot package in Python:

```

In [10]: import numpy as np
%matplotlib inline
import matplotlib.pyplot as plt
eta = 6.63e-34/2/np.pi #Reduced Plank constant in eV.s
q = 1.6e-19
L=2e-9
m = 9.11e-31 #Assuming the particle mass is equal to a free electron

Uo=q
N=100
E1=5*q
dE=1e-2*q
E=np.arange(0,E1,dE)
k=np.sqrt(2*m*E/(eta**2))
alpha=np.sqrt(2*m*(-Uo-E)/(eta**2)+0j)

#print(k)
#print(a)

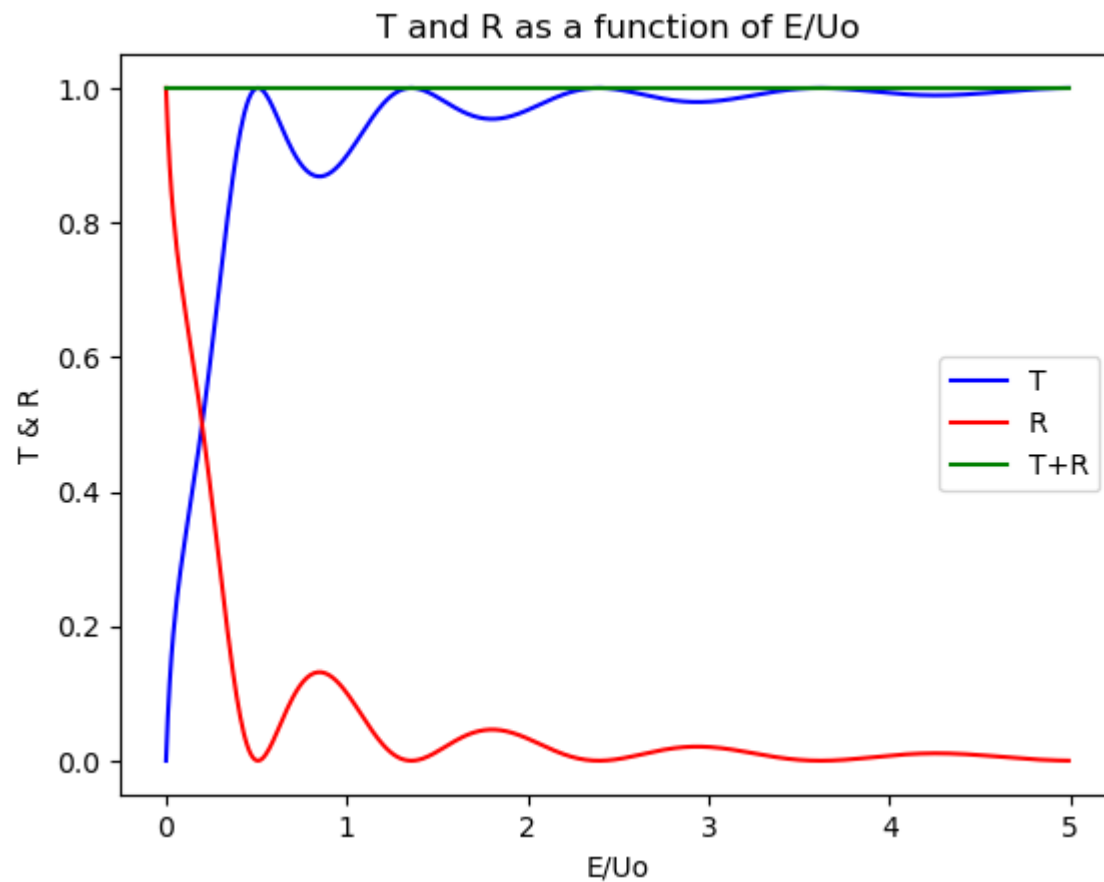
#print(np.exp(1j*np.pi))

t=-4j*alpha*k/((alpha+k*1j)**2*np.exp(-alpha*L)-(alpha-k*1j)**2*np.exp(alpha*L))*np.exp(-1j*k*L)
T=abs(t)**2
r=(alpha**2+k**2)*(np.exp(-alpha*L)-np.exp(alpha*L))/((alpha+k*1j)**2*np.exp(-alpha*L)-(alpha-k*1j)**2*np.exp(alpha*L))
R=abs(r)**2

plt.figure()
plt.plot(E/Uo, T, color='b', ls='--')
plt.plot(E/Uo, R, color='r', ls='--')
plt.plot(E/Uo, T+R, color='g', ls='--')
plt.legend(['T', 'R', 'T+R'])
plt.title('T and R as a function of E/Uo')
plt.xlabel('E/Uo')
plt.ylabel('T & R')

```

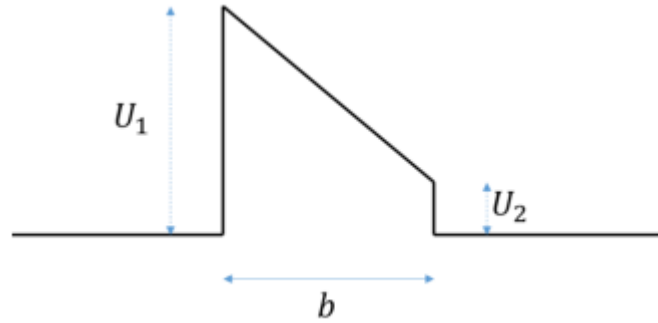
Out[10]: Text(0, 0.5, 'T & R')



Chapter-10 P9 :

Calculate the transmission probability of a triangular barrier as shown in the figure below for energies between 10meV and 1eV . The values of the parameters are $b = 5\text{nm}$, $U_1 = 800\text{meV}$ and $U_2 = 200\text{meV}$.

(You may want to break this down into many rectangular barriers with varying width and heights.)



Answer

According to the 10.7 in the textbook, the scattering matrix M of a transmission through a system consisting of multiple barriers can be broken into small piece of barriers:

$$M = M_1 M_2 \dots M_n$$

where M_n can be written as:

$$M_n = \frac{1}{2ik} \begin{pmatrix} ik + \alpha & ik - \alpha \\ ik - \alpha & ik + \alpha \end{pmatrix} \frac{1}{2\alpha} \begin{pmatrix} (\alpha + i\beta)e^{-\alpha L_n} & (\alpha - i\beta)e^{-\alpha L_n} \\ (\alpha - i\beta)e^{+\alpha L_n} & (\alpha + i\beta)e^{+\alpha L_n} \end{pmatrix}$$

where k , α , and β is related to the shape of the rectangular barrier at any specific location x :

$$k = \sqrt{\frac{2mE}{\hbar^2}}$$

$$\alpha = \sqrt{\frac{2m(qU(x) - E)}{\hbar^2}}$$

$$\beta = \sqrt{\frac{2mE}{\hbar^2}}$$

The transmission probability can be calculated from the cascaded matrix:

$$T = \left| \frac{1}{M_{11}} \right|^2$$

This problem will be solved in Python code below.


```

In [11]: q=1.6e-19
b=5e-9
U1=0.8*q
U2=0.2*q
m=9.1e-31
eta = 6.63e-34/2/np.pi #Reduced Plank constant in eV.s

Num=401;
Ux=np.linspace(U1,U2,Num)
#print(Ux)
Ln=b/(Num-1)

Ta=[]
Ra=[]
Ein=np.arange(10e-3*q,5*q,11.1e-3*q)
#Ein=[10e-3*q, 1000e-3*q]
#E=10e-3*q
for E in Ein:
    k=np.sqrt(2*m*E/(eta**2))
    alphax=np.sqrt(2*m*(Ux-E)/(eta**2)+0j)
    beta=k
    Cx=1/(2*1j*k)*1/(2*alphax)
    M=np.eye(2)
    for i in range(Num):
        A11=1j*k+alphax[i]
        A12=1j*k-alphax[i]
        A21=1j*k-alphax[i]
        A22=1j*k+alphax[i]
        A=np.array([[A11, A12], [A21, A22]])
        B11=(alphax[i]+1j*beta)*np.exp(-alphax[i]*Ln)
        B12=(alphax[i]-1j*beta)*np.exp(-alphax[i]*Ln)
        B21=(alphax[i]-1j*beta)*np.exp(alphax[i]*Ln)
        B22=(alphax[i]+1j*beta)*np.exp(alphax[i]*Ln)
        B=np.array([[B11, B12], [B21, B22]])
        Mn=Cx[i]*A @ B
        M = M @ Mn
        T=abs(1/M[0,0])**2
        R=abs(M[1,0]/M[0,0])**2

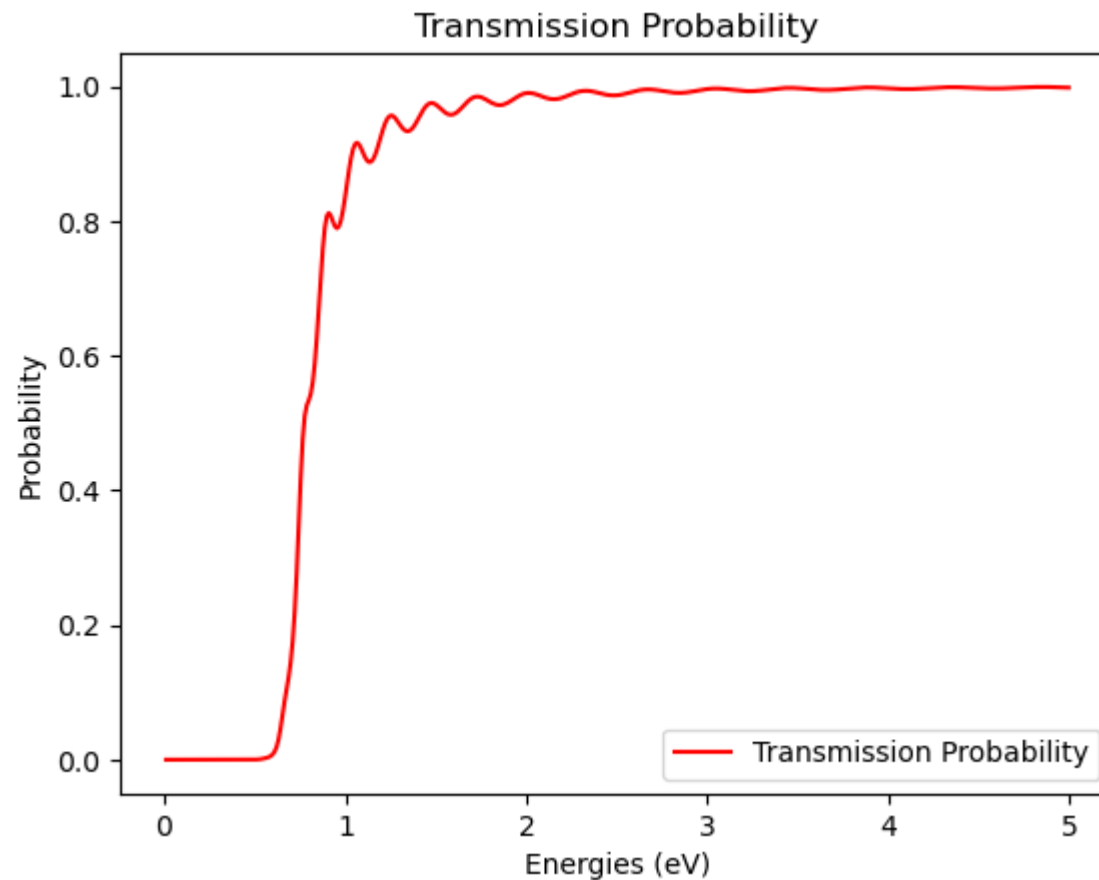
    Ta=Ta+[T]
    Ra=Ra+[R]

#print(Ta)

```

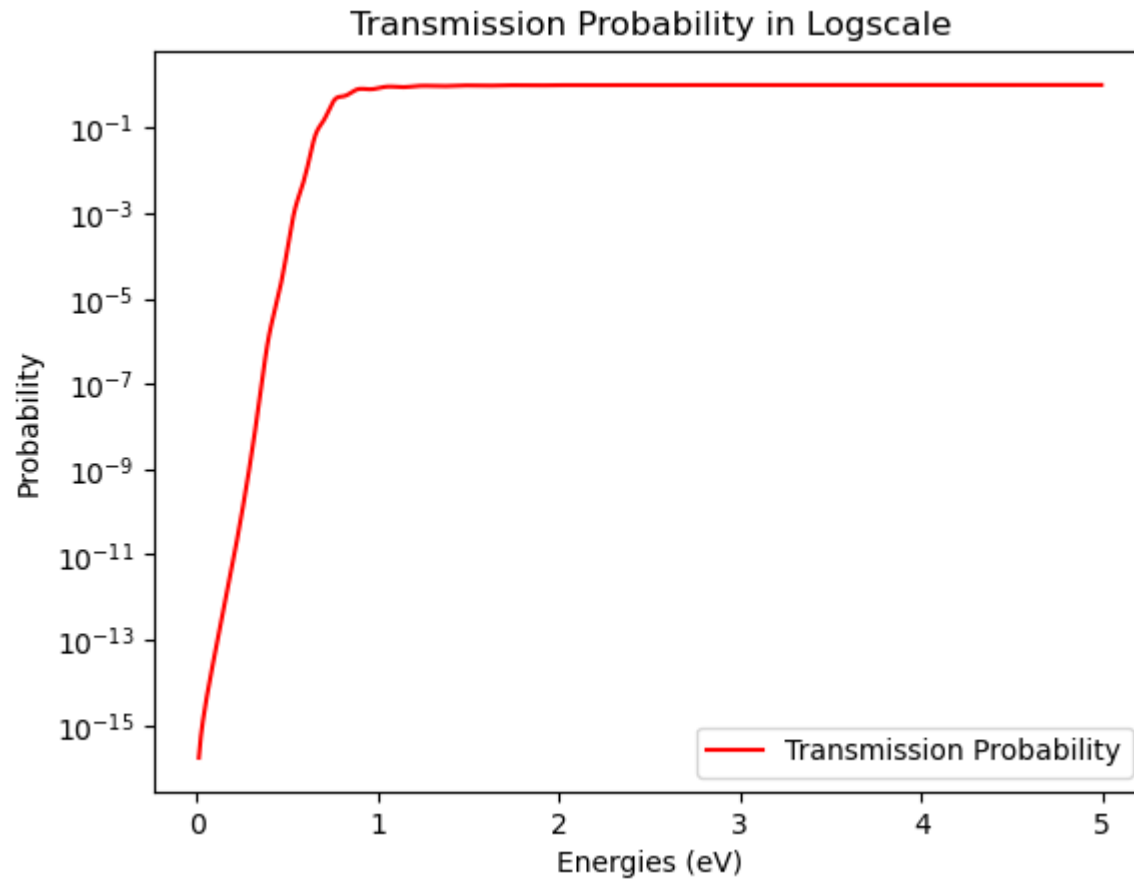
```
plt.figure()
plt.plot(Ein/q, Ta, color='r', ls='-')
#plt.plot(Ein/q, Ra, color='b', ls='-')
plt.legend(['Transmission Probability', 'Reflection Probability'])
plt.title('Transmission Probability')
plt.xlabel('Energies (eV)')
plt.ylabel('Probability')
```

Out[11]: Text(0, 0.5, 'Probability')




```
In [12]: plt.figure()
plt.yscale("log")
plt.plot(Ein/q, Ta, color='r', ls='-')
#plt.plot(Ein/q, Ra, color='b', ls='-')
plt.legend(['Transmission Probability', 'Reflection Probability'])
plt.title('Transmission Probability in Logscale')
plt.xlabel('Energies (eV)')
plt.ylabel('Probability')
```

Out[12]: Text(0, 0.5, 'Probability')



Chapter-11 P1 :

Derive expressions for energy levels and wave functions for a particle of effective mass M on an infinitesimally thin cylindrical shell (an example is an ultrathin aluminum foil rolled up as a cylinder) with radius R and length L . The potential energy of the particle on the cylinder is a constant U_o . The potential energy outside the cylinder is infinity.

Answer:

Based on the description of the problem, we can rewrite the H in a cylindrical coordinate:

$$H = -\frac{\hbar^2}{2m_c} \frac{1}{R^2} \frac{d^2}{d\theta^2} - \frac{\hbar^2}{2m_c} \frac{d^2}{dz^2} + U(\theta, z)$$

where

$$U(\theta, z) = \begin{cases} U_o & 0 < z < L \\ \infty & \text{Otherwise} \end{cases}$$

The wavefunction ψ in $H\psi(\theta, z) = E\psi(\theta, z)$ can be expressed as $\psi(\theta, z) = \Theta(\theta)Z(z)$, where

$$-\frac{\hbar^2}{2m_c} \frac{d^2}{dz^2} = \epsilon_3 Z(z)$$

with potential being zero for $0 < z < L$ and ∞ outside. The $Z(z)$ can be solved as:

$$Z(z) = \sqrt{\frac{2}{L}} \sin\left(\frac{n\pi}{L} z\right) \quad \text{and} \quad \epsilon_3 = \frac{\hbar^2}{2m_c} \left(\frac{n\pi}{L}\right)^2$$

The general solution for $\Theta(\theta)$ is:

$$\Theta(\theta) = e^{ik_1 R\theta}$$

Since $\Theta(\theta)$ has a boundary condition $e^{ik_1 \theta R} = e^{ik_1 (\theta+2\pi)R}$. Then we will have

$$e^{ik_1 2\pi R} = 1$$

$$k_1 = \frac{2\pi}{2\pi R} p = \frac{l}{R} \quad l = 0, \pm 1, \pm 2$$

Then ψ is:

$$\psi(\theta, z) = e^{il\theta} \sqrt{\frac{2}{L}} \sin\left(\frac{n\pi}{L} z\right), \quad l = 0, \pm 1, \pm 2$$

The energy level in the conduction band is :

$$E = E_c + \frac{\hbar^2}{2m_c} \left(\frac{n\pi}{L}\right)^2, \quad n = 0, \pm 1, \pm 2$$

Similarly, the energy level in the valence band is :

$$E = E_v - \frac{\hbar^2}{2m_v} \left(\frac{n\pi}{L} \right)^2, \quad n = 0, \pm 1, \pm 2$$

Chapter-11 P3 :

You have a bulk semiconductor with a bandgap of $0.7eV$. Assume that the effective mass of both electrons and holes is $9.1 \times 10^{-31}kg$. Furthermore, this semiconductor is known to be a poor emitter of light both at $500nm$ and $8000nm$. How would you engineer this structure so that it emits light with a wavelength of (a) $500nm$ and (b) $8000nm$? Find the nanostructure dimensions to achieve (a) and (b). Your design can be based on quantum wells, dots or nanowires.

Answer

(a) For $\lambda = 500nm$, we can calculate a required bandgap energy from

$$E = \hbar\omega = hf = \frac{hc}{\lambda} = \frac{6.626 * 10^{-34} * 3 * 10^8}{500 * 10^{-9}} = 3.9756 * 10^{-19}J = 2.485eV$$

In a bulk semiconductor, at the bottom of the band, we have:

$$E_c - E_v = 0.7eV$$

In a quantum dot structure, at the bottom of the band, we have

$$E_{c,qd} - E_{v,qd} = 0.7 + \frac{\hbar^2}{2} \left(\frac{1}{m_c} + \frac{1}{m_v} \right) \left[\left(\frac{\pi}{L_1} \right)^2 + \left(\frac{\pi}{L_2} \right)^2 + \left(\frac{\pi}{L_3} \right)^2 \right]$$

In order to emit light with a wavelength of $500nm$, L_1 , L_2 , and L_3 in a quantum dot needs to satisfy:

$$\frac{\hbar^2}{2} \left(\frac{1}{m_c} + \frac{1}{m_v} \right) \left[\left(\frac{\pi}{L_1} \right)^2 + \left(\frac{\pi}{L_2} \right)^2 + \left(\frac{\pi}{L_3} \right)^2 \right] = (2.485 - 0.7)eV$$

By solving the equation above, we can find $L_1 = L_2 = L_3 \approx 0.95nm$ can meet the requirement.

(b) For $\lambda = 8000nm$, we can calculate a required bandgap energy from

$$E = \hbar\omega = hf = \frac{hc}{\lambda} = \frac{6.626 * 10^{-34} * 3 * 10^8}{8000 * 10^{-9}} = 2.485 * 10^{-20}J = 0.155eV$$

In a bulk semiconductor, at the bottom of the band, we have:

$$E_c - E_v = 0.7eV$$

The required bandgap energy is less than the energy in a bulk semiconductor. Thus, in this case, the energy difference between two conduction bands need to be used to emit light with a wavelength of 800nm. I will still choose to use a quantum dot to achieve this. Assuming $L_1 = L_2 = L_3 = L$, the energy difference between the $E_{1,1,1}$ and $E_{2,1,1}$ should be equal to $0.155eV$:

$$\frac{\hbar^2}{2} \frac{1}{m_c} \left(\frac{\pi}{L}\right)^2 = 0.155eV$$

Then by solving the equation above, we can find $L_1 = L_2 = L_3 \approx 1.56nm$ can meet the requirement.